



AP

Docket No.: 050432-0293 (G0355)

PATENT

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of : Customer Number: 20277  
Cyrus E. TABERY, et al. : Confirmation Number: 1966  
Application No.: 10/021,782 : Group Art Unit: 2812  
Filed: December 18, 2001 : Examiner: Isaac, Stanetta D.  
For: SCANNING LASER THERMAL ANNEALING

**REPLY BRIEF PURSUANT TO 37 C.F.R. § 41.41**

Mail Stop Appeal Brief - Patents  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

The following Remarks are respectfully submitted in response to new issues raised in the Examiner's Answer dated July 11, 2006, pursuant to 37 C.F.R. § 41.41.

**REMARKS**

Appellants traverse new issues raised in the Examiner's Response to Argument in the Examiner's Answer. On page 10 of the Examiner's Answer, the Examiner alleged that the laser annealing process of Embodiment 2 is different from the laser annealing process of Embodiment 1. The Examiner's position is not supported by the Yamazaki disclosure of Embodiment 1 and Embodiment 2.

The disclosed difference between Embodiment 1 and Embodiment 2 are the manner of formation of the silicon oxide film and the film thickness. In Embodiment 1, the silicon oxide film is formed at a thickness of 2000 Å on a glass substrate by plasma CVD using TEOS as a